COMPLEMENTARY PAIR ENHANCEMENT MODE MOSFET

Product Summary

Device	$V_{(BR)DSS}$	$R_{DS(ON)}$ max	I_D max T_C = 25°C
Q1	30V	21mΩ @ V_{GS} = 10V	14A
		32mΩ @ V_{GS} = 4.5V	14A
Q2	-30V	39mΩ @ V_{GS} = -10V	-14A
		53mΩ @ V_{GS} = -4.5V	-14A

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 standards for High Reliability**

Description and Applications

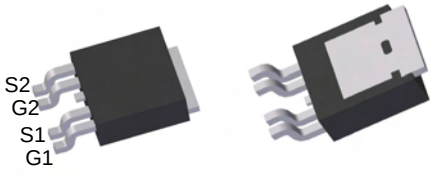
This MOSFET has been designed to minimize the on-state resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Motor control
- Power Management Functions
- DC-DC Converters
- Backlighting

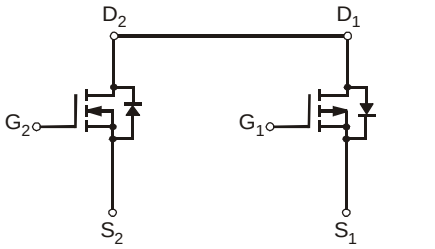
Mechanical Data

- Case: TO252-4
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See diagram
- Terminals: Finish – Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.027 grams (approximate)

TO252-4



Top View Bottom View



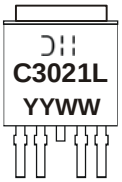
N-Channel MOSFET P-Channel MOSFET

Ordering Information (Note 4)

Part Number	Case	Packaging
DMC3021LK4-13	TO252-4	2500/Tape & Reel

Notes:
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
2. See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at http://www.diodes.com

Marking Information



= Manufacturer's Marking
C3021L = Product Type Marking Code
YYWW = Date Code Marking
YY = Year (ex: 11 = 2011)
WW = Week (01 - 53)

Maximum Ratings N-CHANNEL – Q1 @T_A = 25°C unless otherwise specified

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V_{DSS}	30	V
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current (Note 5) V_{GS} = 10V	Steady State	T_A = 25°C T_A = 70°C	I_D	9.4 7.5	A
Continuous Drain Current (Note 6 & 7) V_{GS} = 10V	Steady State	T_C = 25°C T_C = 70°C	I_D	14 14	A
Pulsed Drain Current (Note 8)			I_{DM}	70	A

Maximum Ratings P-CHANNEL – Q2 @T_A = 25°C unless otherwise specified

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V_{DSS}	-30	V
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current (Note 5) V_{GS} = -10V	Steady State	T_A = 25°C T_A = 70°C	I_D	-6.8 -5.3	A
Continuous Drain Current (Note 6 & 7) V_{GS} = -10V	Steady State	T_C = 25°C T_C = 70°C	I_D	-14 -14	A
Pulsed Drain Current (Note 8)			I_{DM}	-50	A

Thermal Characteristics @T_A = 25°C unless otherwise specified

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)	T_A = 25°C	P_D	2.7	W
	T_A = 70°C		1.7	
Total Power Dissipation (Note 6)	T_C = 25°C		22	
	T_C = 70°C		14	
Thermal Resistance, Junction to Ambient (Note 5)	Steady state	$R_{\theta JA}$	46	°C/W
Thermal Resistance, Junction to Case (Note 6)	Steady state	$R_{\theta JC}$	5.5	
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, on 1inch square copper plate.
6. Device mounted on infinite heatsinke, Tc is measured on the bottom of package
7. The maximum current rating is limited by bond-wires
8. Device mounted on minimum recommended pad layout test board, 10µs pulse duty cycle = 1%.

Electrical Characteristics N-CHANNEL – Q1 @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 9)						
Drain-Source Breakdown Voltage	BV_{DSS}	30	-	-	V	V_{GS} = 0V, I_D = 250μA
Zero Gate Voltage Drain Current @T_c = 25°C	I_{DSS}	-	-	1.0	μA	V_{DS} = 30V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	-	-	±100	nA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 9)						
Gate Threshold Voltage	$V_{GS(th)}$	1	1.5	2.1	V	V_{DS} = V_{GS}, I_D = 250μA
Static Drain-Source On-Resistance	$R_{DS\ (ON)}$	-	14	21	mΩ	V_{GS} = 10V, I_D = 7A
		-	18	32		V_{GS} = 4.5V, I_D = 5.6A
Forward Transfer Admittance	$\|Y_{fs}\|$	-	8.5	-	S	V_{DS} = 5V, I_D = 7A
Diode Forward Voltage	V_{SD}	-	0.7	1.0	V	V_{GS} = 0V, I_S = 1A
DYNAMIC CHARACTERISTICS (Note 10)						
Input Capacitance	C_{iss}	-	751	-	pF	V_{DS} = 10V, V_{GS} = 0V, f = 1.0MHz
Output Capacitance	C_{oss}	-	121	-	pF	
Reverse Transfer Capacitance	C_{rss}	-	110	-	pF	
Gate Resistance	R_g	-	1.5	-	Ω	V_{DS} = 10V, V_{GS} = 0V,f = 1.0MHz
Total Gate Charge (4.5V)	Q_g	-	9	-	nC	V_{GS} = 10V, V_{DS} = 15V, I_D = 6A
Total Gate Charge (10V)	Q_g	-	17.4	-	nC	
Gate-Source Charge	Q_{gs}	-	2.2	-	nC	
Gate-Drain Charge	Q_{gd}	-	3	-	nC	
Turn-On Delay Time	$t_{D(on)}$	-	2.5	-	ns	V_{DD} = 15V, V_{GS} = 10V, R_G = 6Ω, R_L = 1.8Ω, I_D = 6.7A
Turn-On Rise Time	t_r	-	6.6	-	ns	
Turn-Off Delay Time	$t_{D(off)}$	-	19.0	-	ns	
Turn-Off Fall Time	t_f	-	6.3	-	ns	

Notes: 9. Short duration pulse test used to minimize self-heating effect
10. Guaranteed by design. Not subject to product testing

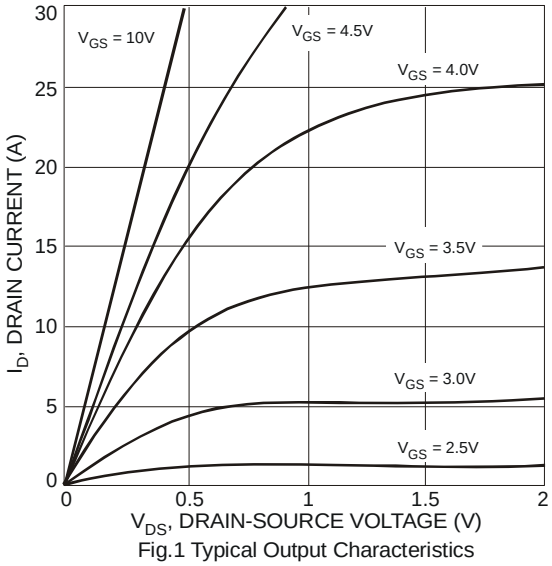


Fig.1 Typical Output Characteristics

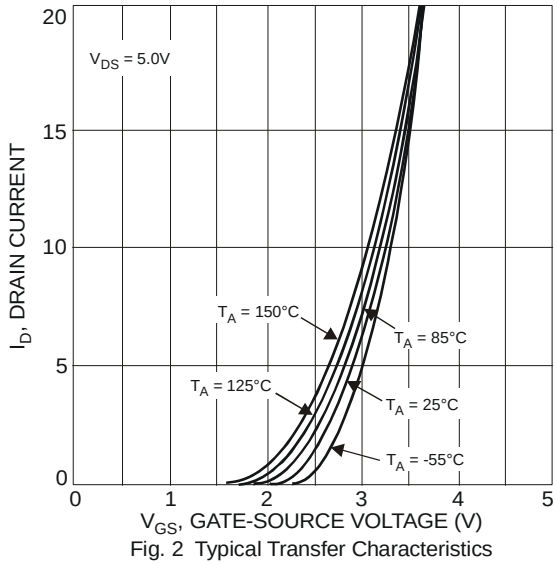


Fig. 2 Typical Transfer Characteristics

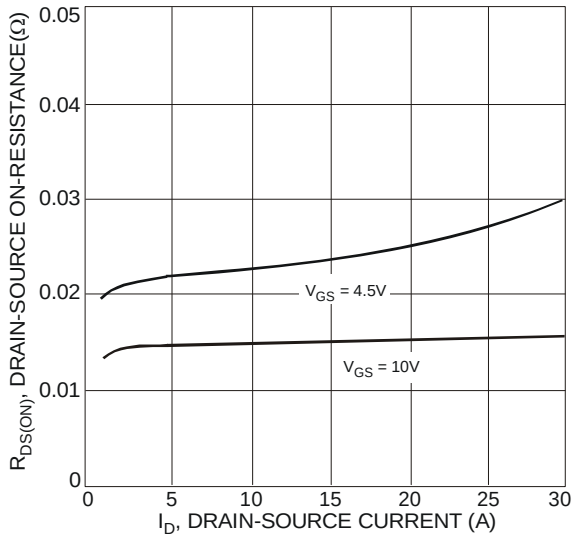


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

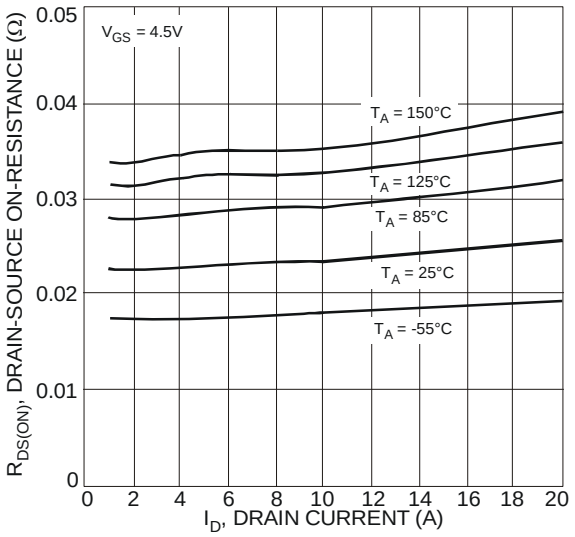


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

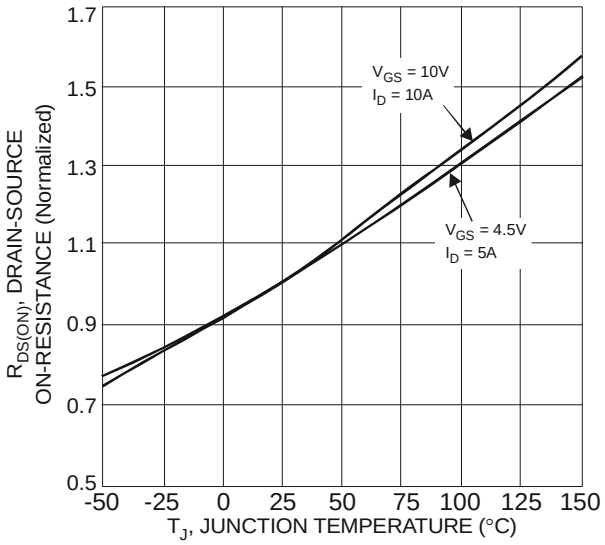


Fig. 5 On-Resistance Variation with Temperature

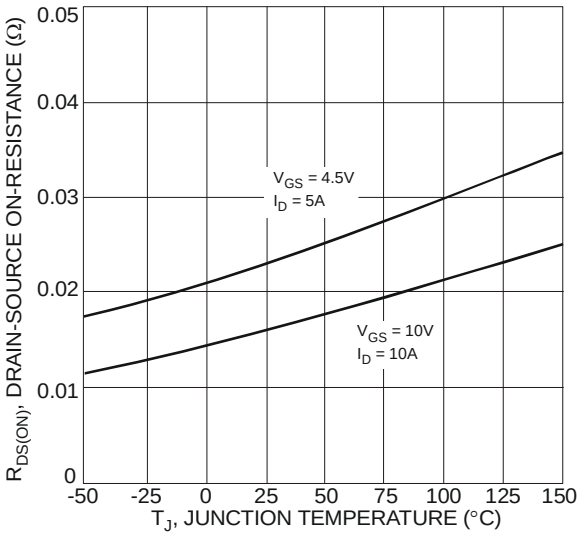


Fig. 6 On-Resistance Variation with Temperature

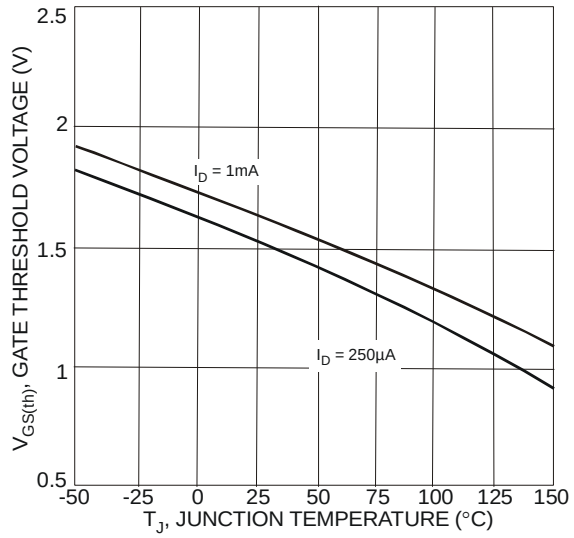


Fig. 7 On-Resistance Variation with Temperature

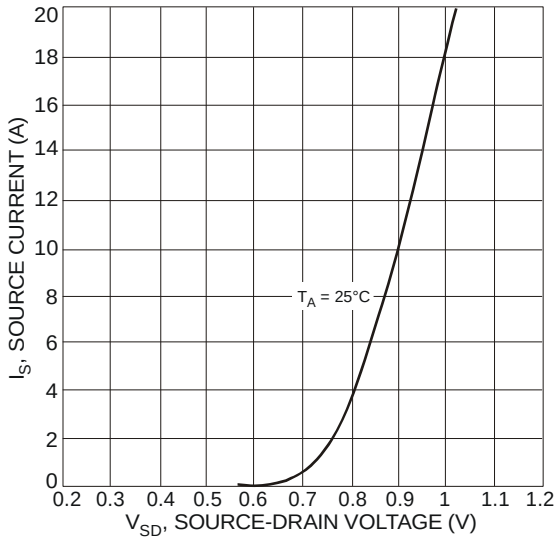


Fig. 8 Diode Forward Voltage vs. Current

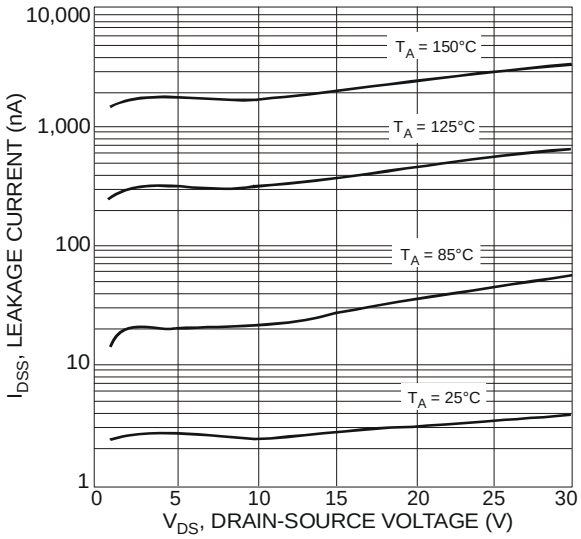


Fig. 9 Typical Drain-Source Leakage Current vs. Voltage

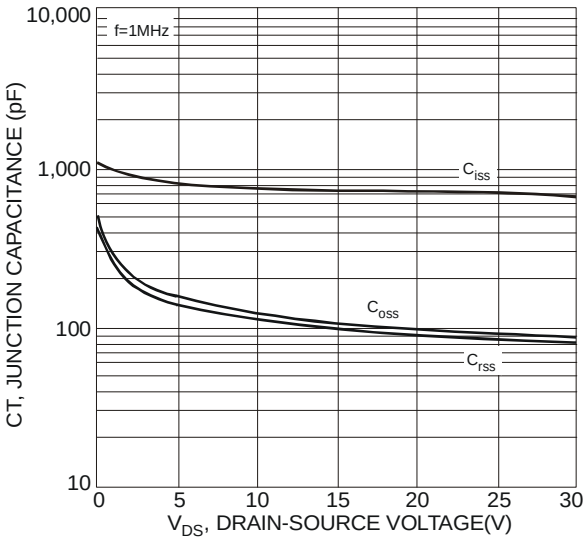


Fig. 10 Typical Junction Capacitance

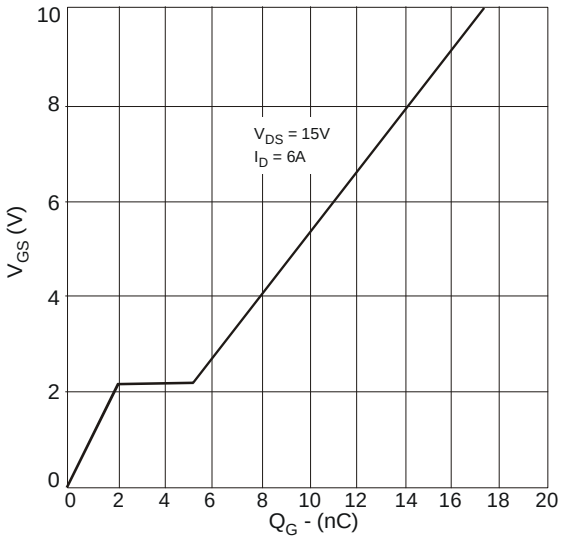


Fig. 11 Gate Charge Characteristics

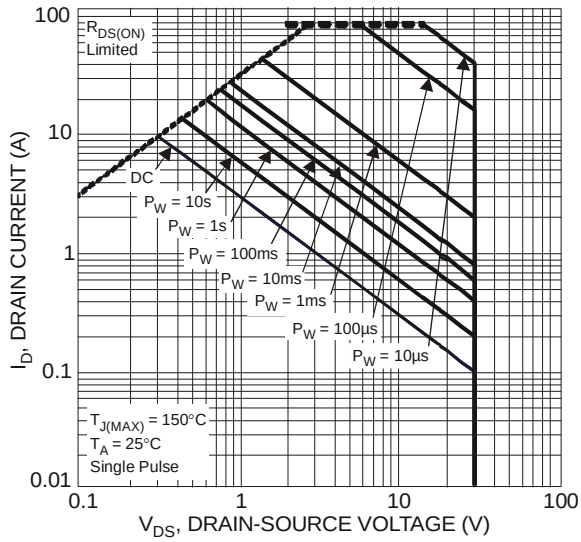


Fig. 12 SOA, Safe Operation Area

Electrical Characteristics P-CHANNEL – Q2 @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 9)						
Drain-Source Breakdown Voltage	BV_{DSS}	-30	-	-	V	V_{GS} = 0V, I_D = -250µA
Zero Gate Voltage Drain Current @T_c = 25°C	I_{DSS}	-	-	-1	µA	V_{DS} = -30V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	-	-	±100	nA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 9)						
Gate Threshold Voltage	$V_{GS(th)}$	-1	-1.7	-2.2	V	V_{DS} = V_{GS}, I_D = -250µA
Static Drain-Source On-Resistance	$R_{DS\ (ON)}$	-	30	39	mΩ	V_{GS} = -10V, I_D = -4.3A
		-	42	53		V_{GS} = -4.5V, I_D = -3.7A
Forward Transfer Admittance	$\|Y_{fs}\|$	-	10	-	S	V_{DS} = -5V, I_D = -4.3A
Diode Forward Voltage	V_{SD}	-	-0.75	-1.0	V	V_{GS} = 0V, I_S = -1A
DYNAMIC CHARACTERISTICS (Note 10)						
Input Capacitance	C_{iss}	-	1039	-	pF	V_{DS} = -10V, V_{GS} = 0V, f = 1.0MHz
Output Capacitance	C_{oss}	-	144	-	pF	
Reverse Transfer Capacitance	C_{rss}	-	134	-	pF	
Gate Resistance	R_g	-	13	-	Ω	V_{DS} = 0V, V_{GS} = 0V,f = 1.0MHz
Total Gate Charge (4.5V)	Q_g	-	10.1	-	nC	V_{GS} = -10V, V_{DS} = -15V, I_D = -6A
Total Gate Charge (10V)	Q_g	-	21.1	-	nC	
Gate-Source Charge	Q_{gs}	-	2.8	-	nC	
Gate-Drain Charge	Q_{gd}	-	3.2	-	nC	
Turn-On Delay Time	$t_{D(on)}$	-	10.1	-	ns	V_{DS} = -15V, V_{GS} = -10V, R_G = 6Ω, I_D = -1A
Turn-On Rise Time	t_r	-	6.5	-	ns	
Turn-Off Delay Time	$t_{D(off)}$	-	50.1	-	ns	
Turn-Off Fall Time	t_f	-	22.2	-	ns	

Notes: 9. Short duration pulse test used to minimize self-heating effec
10. Guaranteed by design. Not subject to product testing.

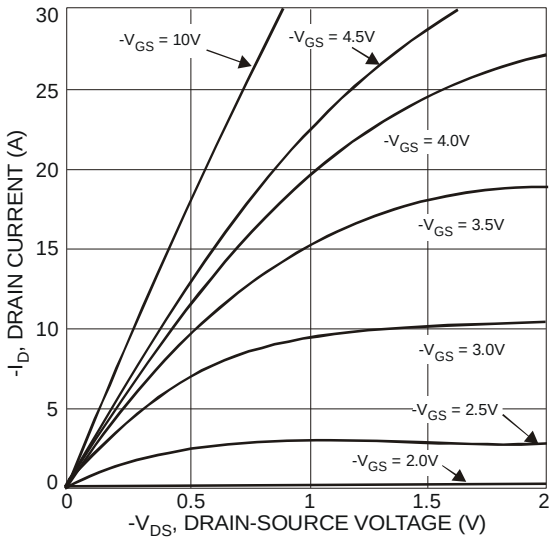


Fig.13 Typical Output Characteristics

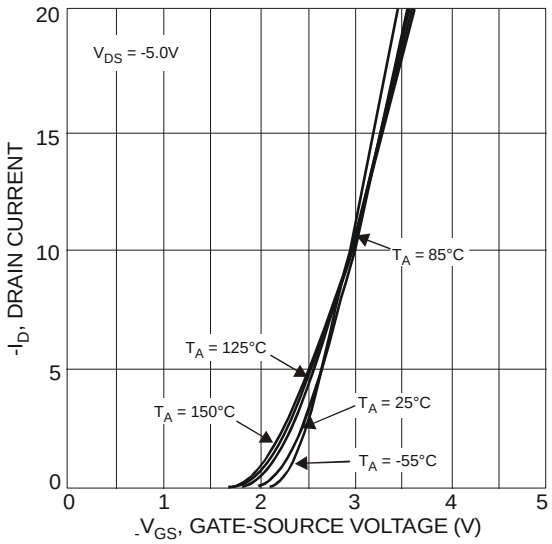


Fig. 14 Typical Transfer Characteristics

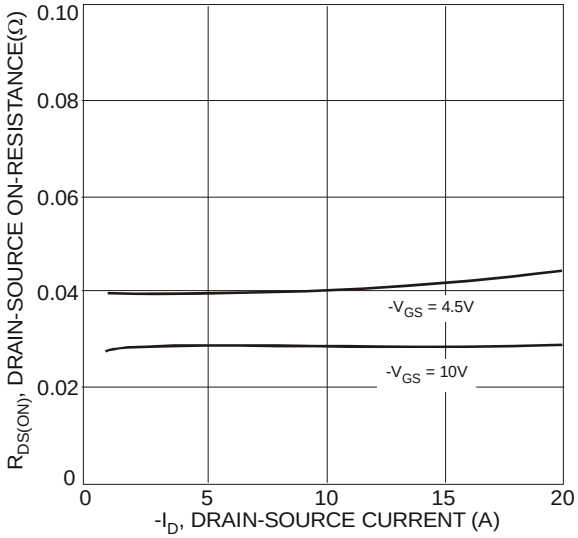


Fig. 15 Typical On-Resistance vs. Drain Current and Gate Voltage

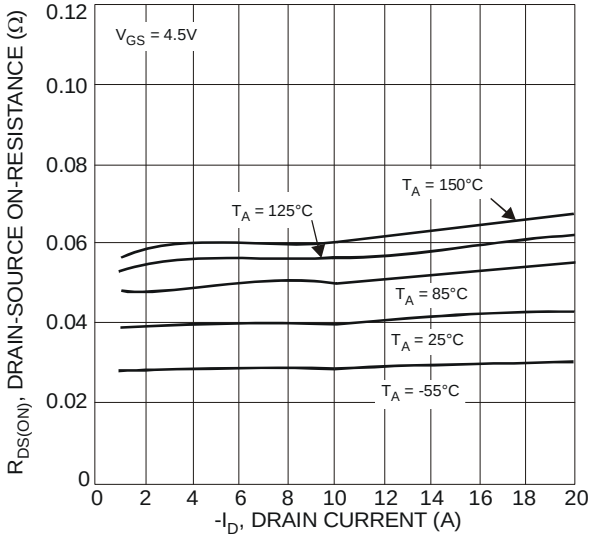


Fig. 16 Typical On-Resistance vs. Drain Current and Temperature

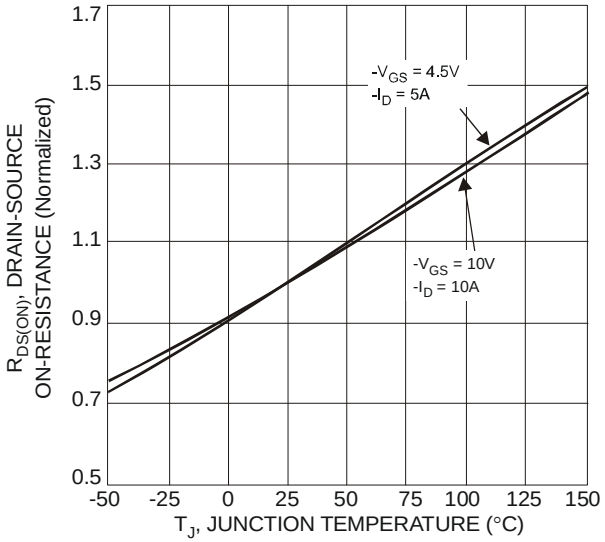


Fig. 17 On-Resistance Variation with Temperature

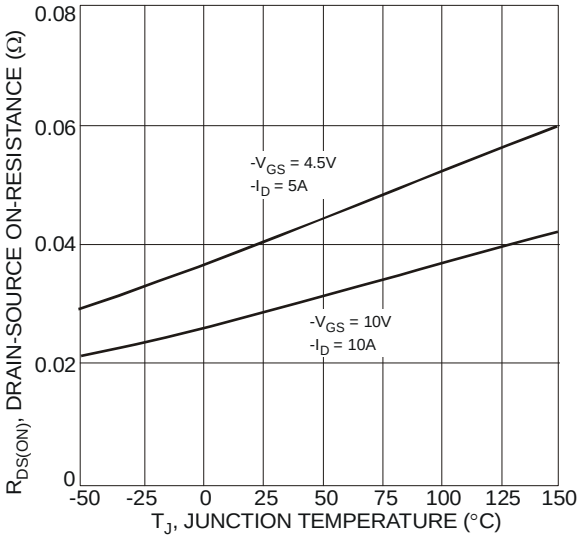


Fig. 18 On-Resistance Variation with Temperature

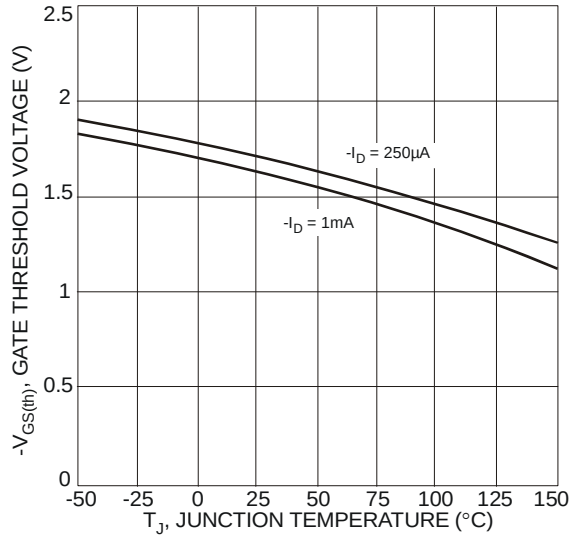


Fig. 19 On-Resistance Variation with Temperature

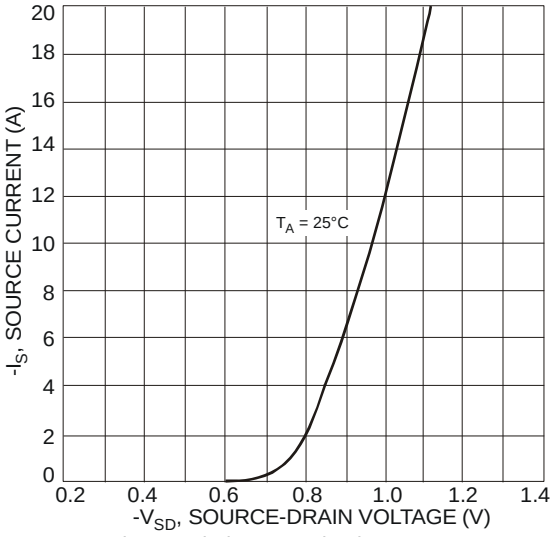


Fig. 20 Diode Forward Voltage vs. Current

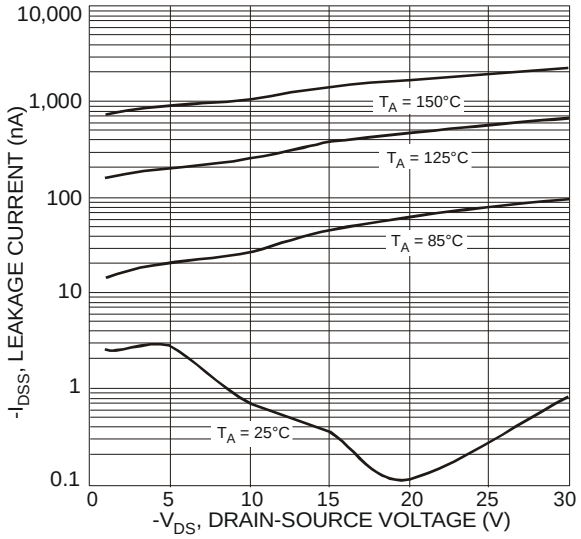


Fig. 21 Typical Drain-Source Leakage Current vs. Voltage

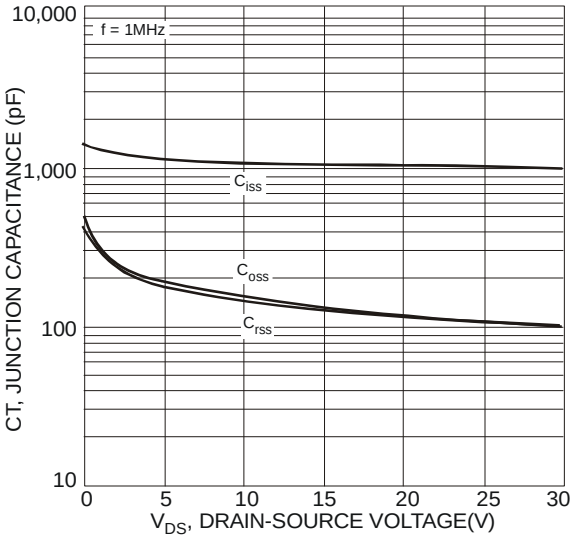


Fig. 22 Typical Junction Capacitance

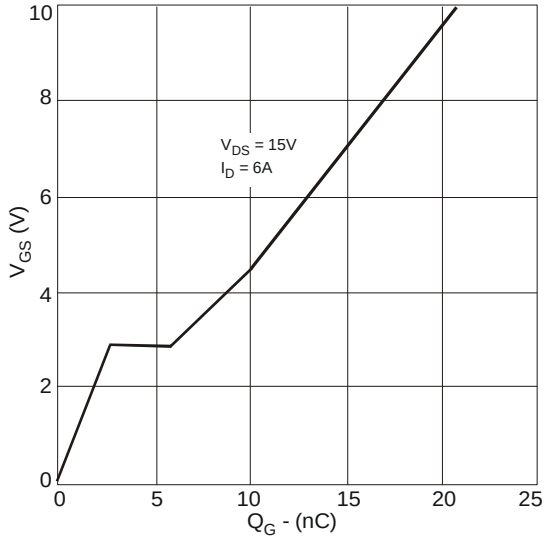


Fig. 23 Gate Charge Characteristics

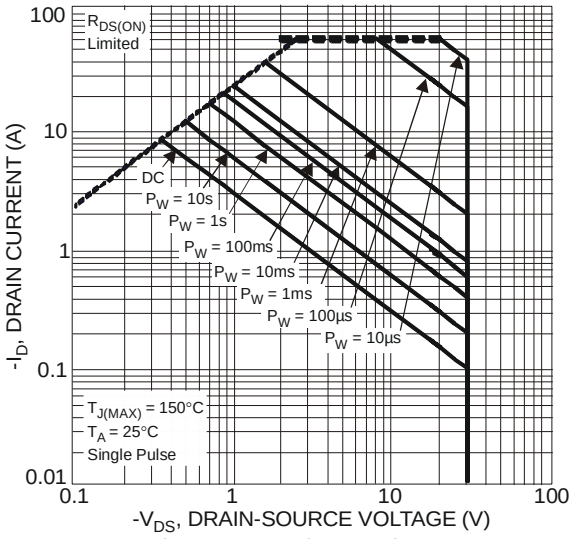


Fig. 24 SOA, Safe Operation Area

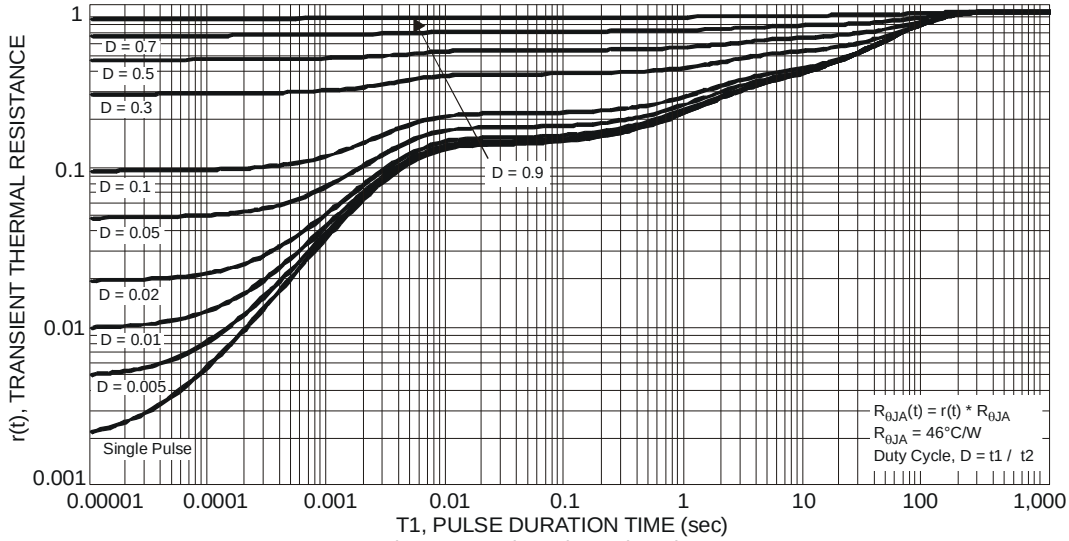
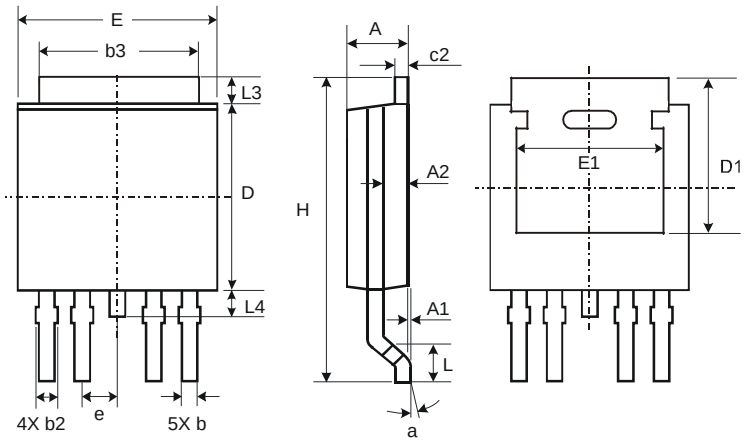


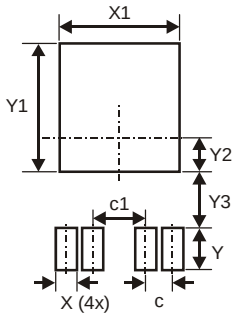
Fig. 25 Transient Thermal Resistance

Package Outline Dimensions



TO252-4			
Dim	**Min**	**Max**	**Typ**
A	2.19	2.39	2.29
A1	0.00	0.13	0.08
A2	0.97	1.17	1.07
b	0.51	0.71	0.583
b2	0.61	0.79	0.70
b3	5.21	5.46	5.33
c2	0.45	0.58	0.531
D	6.00	6.20	6.10
D1	5.21	–	–
e	–	–	1.27
E	6.45	6.70	6.58
E1	4.32	–	–
H	9.40	10.41	9.91
L	1.40	1.78	1.59
L3	0.88	1.27	1.08
L4	0.64	1.02	0.83
a	0°	10°	–
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
c	1.27
c1	2.54
X	1.00
X1	5.73
Y	2.00
Y1	6.17
Y2	1.64
Y3	2.66

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2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.

B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

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- Поставка оригинальных импортных электронных компонентов напрямую с производств Америки, Европы и Азии, а так же с крупнейших складов мира;
- Широкая линейка поставок активных и пассивных импортных электронных компонентов (более 30 млн. наименований);
- Поставка сложных, дефицитных, либо снятых с производства позиций;
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- Помощь Конструкторского Отдела и консультации квалифицированных инженеров;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Поставка электронных компонентов под контролем ВП;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- При необходимости вся продукция военного и аэрокосмического назначения проходит испытания и сертификацию в лаборатории (по согласованию с заказчиком);
- Поставка специализированных компонентов военного и аэрокосмического уровня качества (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Actel, Aeroflex, Peregrine, VPT, Syfer, Eurofarad, Texas Instruments, MS Kennedy, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

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